## REMARKS

The Examiner's Office Action of October 2, 2002 has been received and its contents reviewed. Applicants would like to thank the Examiner for the consideration given to the above-identified application, and for indicating the allowance of claims 60-62, 72-74, 81 and 83.

By the above actions, claims 60, 61, 73, and 84 have been amended and new claims 85-91 have been added. In view of these actions and the following remarks, reconsideration of this application is now requested.

Referring now to the detailed Office Action, claim 84 is rejected under 35 U.S.C. §103(a) as being unpatentable over Masumo et al. (U.S. Patent 5,306,651 – hereafter Masumo) in view of Liu et al. (U.S. Patent 5,147,826 – hereafter Liu).

As amended, claim 84 further recite the allowed features of claim 60 but without the language of "by using a CVD system" recited in line 4 in claim 60, and of "irradiating laser beam to said semiconductor film to improve the crystallinity thereof" recited in lines 13-14 in claim 60. Since amended claim 84 recites the allowable subject matters which the Examiner set forth in the Office Action, claim 84 is now in condition for allowance.

Claims 60, 61, and 73 have been amended to further clarify the claim language.

New claims 85-91 have been amended to further complete the scope of the invention to which Applicants are entitled. New independent claim 86 recites the features of allowed claims without the language of "by using a CVD system" recited in line 4 of claim 72, and of "irradiating laser beam to said semiconductor film to improve the crystallinity thereof" recited in lines 12-13 of claim 72. New independent claims 88 and 90 recite claims 60 and 72, respectively, without the language of "by using a CVD system".

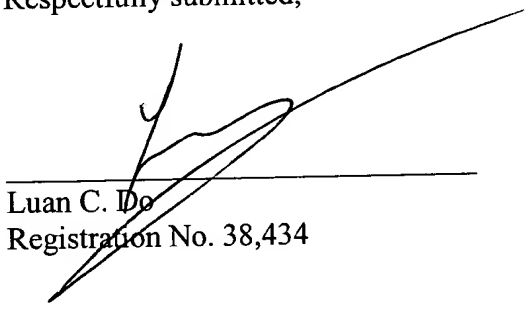
In view of the amendments and arguments set forth above, Applicant respectfully request reconsideration and withdrawal of all the pending rejections.

While the present application is now believed to be in condition for allowance, should the Examiner find some issue to remain unresolved, or should any new issues arise, which could be eliminated through discussions with applicants' representative, then the Examiner is invited to

contact the undersigned by telephone in order that the further prosecution of this application can thereby be expedited.

Lastly, it is noted that a separate Extension of Time Petition accompanies this response along with a check in payment of the requisite extension of time fee. However, should that petition become separated from this Amendment, then this Amendment should be construed as containing such a petition. Likewise, any overage or shortage in the required payment should be applied to Deposit Account No. 19-2380 (740819-488).

Respectfully submitted,



Luan C. Do
Registration No. 38,434

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, VA 22102
(703) 770-9300

**MARKED UP VERSION**

60. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate by using a CVD system;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

disposing a solution in contact with said silicon oxide film, said solution containing a metal being capable of promoting crystallization of said [amorphous silicon] semiconductor film;

heating said semiconductor film and said metal to crystallize said semiconductor film; and

irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

61. (Amended) A method according to claim 60 wherein said CVD system is selected from a plasma CVD system and an LPCVD system.

73. (Amended) A method according to claim 72 wherein said CVD system is selected from a plasma CVD system and an LPCVD system.

84. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;

[depositing] forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

forming a silicon oxide film on said semiconductor film;

[depositing a metal] disposing a solution in contact with [at least a selected portion of] said [semiconductor] silicon oxide film, said solution containing a metal being capable of promoting crystallization of said semiconductor film; and

heating said semiconductor film and said metal to crystallize said semiconductor film[; and

forming a channel region,

wherein said channel region is formed of the crystallized semiconductor film].